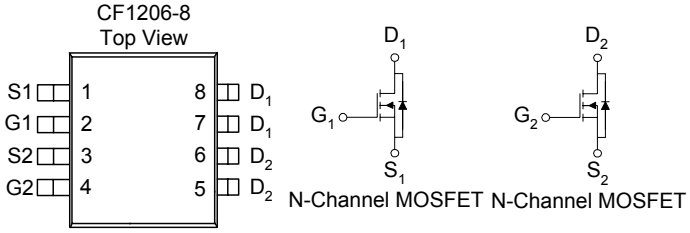
Dual N-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
20	58 @ V_{GS} = 4.5V	5.0
	82 @ V_{GS} = 2.5V	4.2

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe CF1206-8 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		**Symbol**	**Limit**	**Units**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 8	
Continuous Drain Current[a]	T_A=25°C	I_D	5.0	A
	T_A=70°C		4.1	
Pulsed Drain Current[b]		I_{DM}	± 30	
Continuous Source Current (Diode Conduction)[a]		I_S	1.7	A
Power Dissipation[a]	T_A=25°C	P_D	2.1	W
	T_A=70°C		1.3	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Maximum**	**Units**
Maximum Junction-to-Ambient[a]	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W
	Steady State		80	°C/W

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

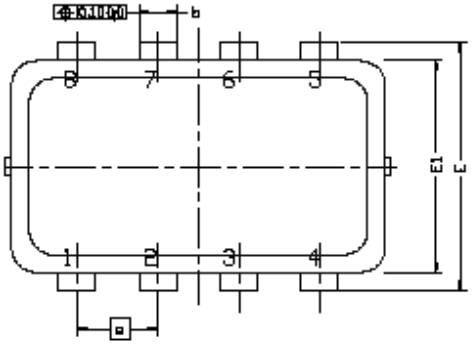
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min	**Typ**	**Max**	
Static						
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 uA	0.7			
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 8 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 16 V, V_{GS} = 0 V			1	uA
		V_{DS} = 16 V, V_{GS} = 0 V, T_J = 55°C			25	
On-State Drain Current[A]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	20			A
Drain-Source On-Resistance[A]	$r_{DS(on)}$	V_{GS} = 4.5 V, I_D = 5 A			58	mΩ
		V_{GS} = 2.5 V, I_D = 4.2 A			82	
Forward Tranconductance[A]	g_{fs}	V_{DS} = 15 V, I_D = 5 A		22		S
Diode Forward Voltage	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V		0.7		V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 5 A		7.5		nC
Gate-Source Charge	Q_{gs}			0.6		
Gate-Drain Charge	Q_{gd}			1.0		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω , I_D = 1 A, V_{GEN} = 4.5 V		22		nS
Rise Time	t_r			40		
Turn-Off Delay Time	$t_{d(off)}$			50		
Fall-Time	t_f			20		
Source-Ddrain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, di/dt = 100 A/uS		40		

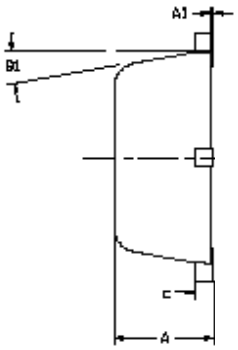
Notes

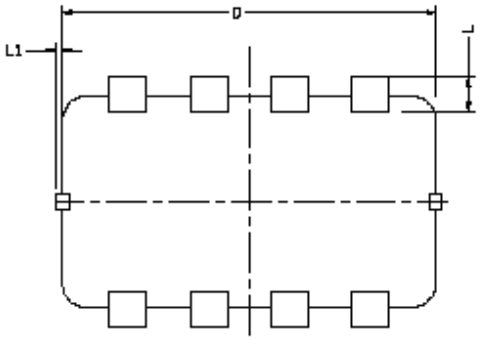
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.

Package Information







DIM.	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.700	0.80	0.900	0.0276	0.0315	0.0354
A1	0.00	---	0.03	0.000	---	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.08	0.152	0.25	0.003	0.006	0.010
D	3.00 BSC			0.118 BSC		
E	2.00 BSC			0.079 BSC		
E1	1.70 BSC			0.067 BSC		
e	0.65 BSC			0.026 BSC		
L	0.20	0.275	0.400	0.008	0.011	0.0157
L1	0	---	0.100	0	---	0.004
θ1	0°	10°	12°	0°	10°	12°